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In the Claims:

1. (currently amended) An oxide sintered body comprising:  
indium oxide ~~and containing~~, titanium, and tin as an impurity,  
wherein the titanium is contained such that the atomic ratio of Ti/In is in a range from  
0.003 to 0.019,  
wherein tin as an impurity in an amount such that the atomic ratio of Sn/In is 0.0025 or  
less, and  
wherein the specific resistance is 1 k Ohm cm or less.
2. (currently amended) ~~the~~ The oxide sintered body of claim 1, wherein the specific resistance is  
 $1 \times 10^{-2}$  Ohm cm or less.
3. cancelled.
4. cancelled.
5. (previously presented) The oxide sintered body of Claim 1, further comprising a main phase  
of one of a crystal phase of indium oxide having a bixbyite type structure with titanium  
contained in solid solution, and of a mixture of a crystal phase of indium oxide having a bixbyite  
type structure with titanium contained in solid solution and a crystal phase of an indium titanate  
compound.
6. (currently amended) A method for providing an oxide sintered body, the oxide sintered body  
comprising indium oxide, tin as an impurity, and titanium, wherein the titanium is contained  
such that an atomic ratio of Ti/In is in a range of 0.003 to 0.019 and wherein a specific resistance  
is 1 k Ohm cm or less, tin as an impurity in an amount such that the atomic ratio of Sn/In is  
0.0025 or less, the method comprising the steps of:  
producing raw materials of indium oxide powder and titanium oxide powder having an  
average particle size of 1  $\mu\text{m}$  or less;  
mixing the raw materials in a wet mill;

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forming the mixed raw materials with a cold isostatic press, and  
sintering the formed and mixed raw materials under oxygen-control.

7. (previously presented) The oxide sintered body of Claim 1, wherein a crystal phase of titanium oxide is not detected by powder X-ray diffraction measurement.
8. (original) The oxide sintered body of Claim 1, wherein the relative density is 95% or greater.
9. (previously presented) The oxide sintered body of Claim 1, wherein a surface roughness  $R_{\max}$  of the surface on a side where sputtering is performed is 3.0  $\mu\text{m}$  or less.
10. (currently amended) A sputtering target, comprising:  
an oxide sintered body comprising indium oxide, tin as an impurity, and titanium,  
wherein the titanium is contained such that an atomic ratio of Ti/In is in a range of 0.003 to 0.019;  
wherein tin as an impurity in an amount such that the atomic ratio of Sn/In is 0.0025 or less, and  
wherein a specific resistance is 1 k  $\Omega\text{cm}$  or less and is applied to ~~the~~ a metal plate for cooling.
11. (previously presented) A sputtering target according to Claim 10 for use in manufacturing a transparent conductive film having a specific resistance  $1 \times 10^{-3} \Omega\text{cm}$  or less.
12. (previously presented) A sputtering target according to Claim 10 for use in manufacturing a low resistant, transparent conductive film having a specific resistance  $5.5 \times 10^{-4} \Omega\text{cm}$  or less.
13. (previously presented) A sputtering target according to Claim 10 for use in manufacturing a transparent conductive film having an average transmittance of infrared rays in the wavelength range from 1000 nm to 1400 nm is at least 60 % for the film itself.

14. (currently amended) A method of manufacturing an oxide transparent electrode film, the method comprising the steps of:

using a sputtering target, the sputtering target comprising an oxide sintered body comprising indium oxide, tin as an impurity, and titanium, wherein the titanium is contained such that an atomic ratio of Ti/In is in a range of 0.003 to 0.019;

wherein tin as an impurity in an amount such that the atomic ratio of Sn/In is 0.0025 or less, and

wherein a specific resistance is 1 k Ohm cm or less and using a DC sputtering method for forming the film.

15. (previously presented) The oxide sintered body of Claim 3, further comprising a main phase of one of a crystal phase of indium oxide having a bixbyite type structure with titanium contained in solid solution, and of a mixture of a crystal phase of indium oxide having a bixbyite type structure with titanium contained in solid solution and a crystal phase of an indium titanate compound.

16. (currently amended) The oxide sintered body of ~~Claim 3~~claim 1, further comprising a main phase of one of a crystal phase of indium oxide having a bixbyite type structure with titanium contained in solid solution, and of a mixture of a crystal phase of indium oxide having a bixbyite type structure with titanium contained in solid solution and a crystal phase of an indium titanate compound.

17. (currently amended) The oxide sintered body of ~~Claim 3~~claim 1, wherein a crystal phase of titanium oxide is not detected by powder X-ray diffraction measurement.

18. (currently amended) ) The oxide sintered body of ~~Claim 4~~claim 1, wherein a crystal phase of titanium oxide is not detected by powder X-ray diffraction measurement.

19. (previously presented) A sputtering target according to Claim 11 for use in manufacturing a transparent conductive film having an average transmittance of infrared rays in the wavelength range from 1000 nm to 1400 nm is at least 60 % for the film itself.

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20. (previously presented) A sputtering target according to Claim 12 for use in manufacturing a transparent conductive film having an average transmittance of infrared rays in the wavelength range from 1000 nm to 1400 nm is at least 60 % for the film itself.

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